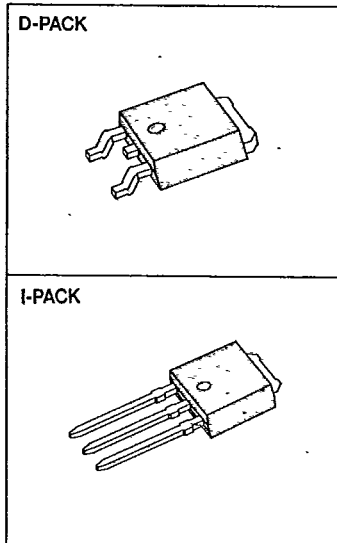


MJD127 PNP SILICON DARLINGTON TRANSISTOR

T-33-31

D-PACK FOR SURFACE MOUNT APPLICATIONS

- High DC Current Gain
- Built-in a Damper Diode at E-C
- Lead Formed for Surface Mount Applications (No Suffix)
- Straight Lead (I-PACK, "-1" Suffix)
- Electrically Similar to Popular TIP127



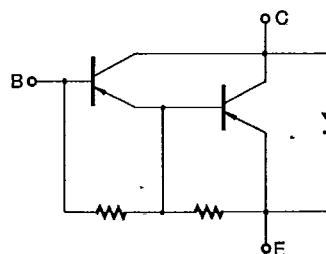
ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V _{CB0}	-100	V
Collector Emitter Voltage	V _{CE0}	-100	V
Emitter Base Voltage	V _{EB0}	-5	V
Collector Current (DC)	I _C	-8	A
Collector Current (Pulse)	I _C	-16	A
Base Current	I _B	-120	A
Collector Dissipation (T _a = 25°C)	P _c	20	W
Collector Dissipation (T _a = 25°C)	P _c	1.75	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-65 ~ 150	°C

ELECTRICAL CHARACTERISTICS (T_a = 25°C)

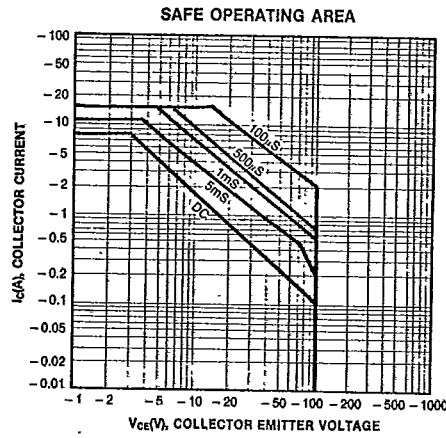
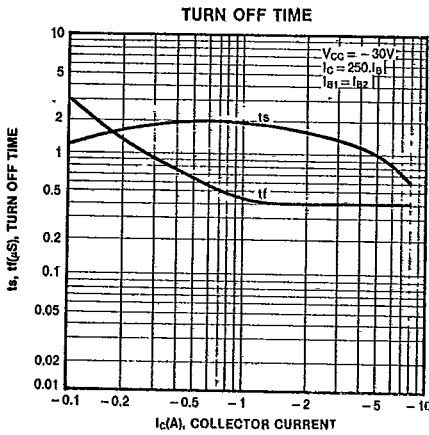
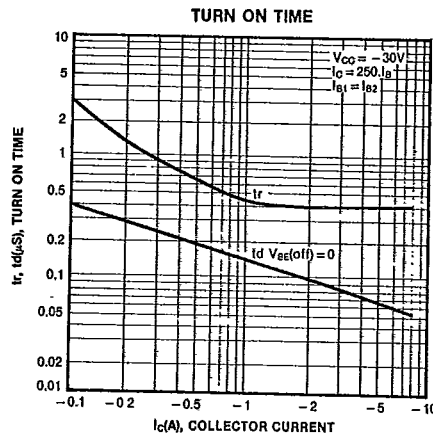
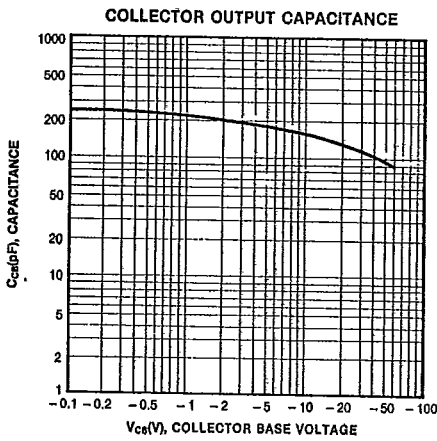
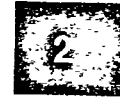
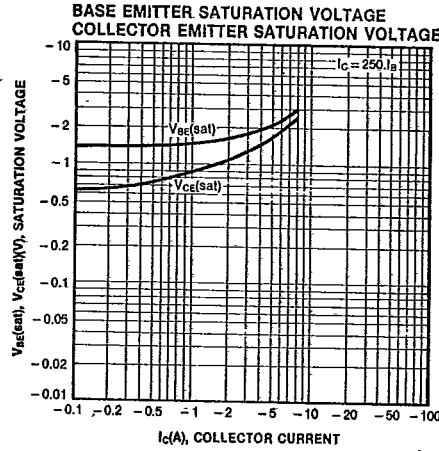
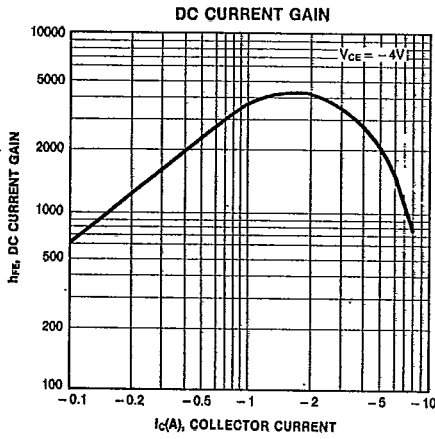
Characteristic	Symbol	Test Condition	Min	Max	Unit
*Collector Emitter Sustaining Voltage	V _{CE0(SUS)}	I _C = -30mA, I _B = 0	-100		V
Collector Cutoff Current	I _{CE0}	V _{CE} = -50V, I _B = 0		-10	μA
Collector Cutoff Current	I _{CB0}	V _{CB} = -100V, I _E = 0		-10	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} = -5V, I _C = 0		-2	mA
*DC Current Gain	h _{FE}	V _{CE} = -4V, I _C = -4A	1000	12K	
		V _{CE} = -4V, I _C = -8A	100		
*Collector Emitter Saturation Voltage	V _{CE(sat)}	I _C = -4A, I _B = -16mA		-2	V
		I _C = -8A, I _B = -80mA		-4	V
*Base Emitter Saturation Voltage	V _{BE(sat)}	I _C = -8A, I _B = -80mA		-4.5	V
*Base Emitter On Voltage	V _{BE(on)}	V _{CE} = -4A, I _C = -4A		-2.8	V
Output Capacitance	C _{OB}	V _{CB} = -10V, I _E = 0 f = 0.1MHz		300	pF

* Pulse Test: PW ≤ 300μS, Duty Cycle ≤ 2%



MJD127 PNP SILICON DARLINGTON TRANSISTOR

T-33-31



MJD127

PNP SILICON DARLINGTON TRANSISTOR

T-33-31

